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## FODM217 Series

## Single Channel, DC Sensing Input, **Phototransistor Optocoupler In** Half-Pitch Mini-Flat 4-Pin Package

The FODM217 Series single channel, DC sensing input, optocoupler consists of one gallium arsenide (GaAs) infrared light emitting diode optically coupled to one phototransistor, in a compact, half-pitch, mini-flat, 4-pin package. The input-output isolation voltage, VISO, is rated at 3,750 VACRMS.

#### **Features**

- Current Transfer Ratio Ranges from 80 to 600% at  $I_F = 5 \text{ mA}$ ,
  - $V_{CE} = 5 V, T_A = 25^{\circ}C$
  - FODM217A 80 to 160%
  - FODM217B 130 to 260%
  - FODM217C 200 to 400%
  - FODM217D 300 to 600%
- Safety and Regulatory Approvals: - UL1577, 3750 VACRMS for 1 min
  - DIN EN/IEC60747-5-5, 565 V Peak Working Insulation Voltage
- Applicable to Infrared Ray Reflow, 260°C

#### **Typical Applications**

- Primarily Suited for DC-DCConverters
- For Ground Loop Isolation, Signal to Noise Isolation
- Communications Adapters, Chargers
- Consumer Appliances, Set Top Boxes
- Industrial Power Supplies, Motor Control, Programmable Logic Control



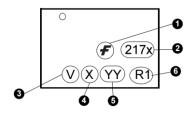
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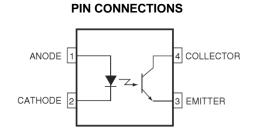


**SOP 4 PINS** 

#### **MARKING DIAGRAM**



- F = Corporate Logo
- 217x = Device Number 2.
- V = DIN EN/IEC60747-5-5 Option 3. 4.
  - X = One-Digit Year Code
- 5. YY = Digit Work Week
- 6. R1 = Assembly Package Code



#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 9 of this data sheet.

## FODM217 Series

#### SAFETY AND INSULATIONS RATING

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter	Characteristics	
Installation Classifications per DIN VDE 0110/1.89 Table 1,	< 150 V <sub>RMS</sub>	I–IV
For Rated Mains Voltage	< 300 V <sub>RMS</sub>	I–III
Climatic Classification	55/110/21	
Pollution Degree (DIN VDE 0110/1.89)	2	
Comparative Tracking Index	175	

Symbol	Parameter	Value	Unit
V <sub>PR</sub>	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$ , Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	904	V <sub>peak</sub>
	Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$ , 100% Production Test with $t_m = 1$ s, Partial Discharge < 5 pC	1060	V <sub>peak</sub>
V <sub>IORM</sub>	Maximum Working Insulation Voltage	565	V <sub>peak</sub>
V <sub>IOTM</sub>	Highest Allowable Over-Voltage	4,000	V <sub>peak</sub>
	External Creepage	≥ 5	mm
	External Clearance	≥ 5	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
Τ <sub>S</sub>	Case Temperature (Note 1)	150	°C
I <sub>S,INPUT</sub>	Input Current (Note 1)	200	mA
P <sub>S,OUTPUT</sub>	Output Power (Note 1)	300	mW
R <sub>IO</sub>	Insulation Resistance at $T_S$ , $V_{IO}$ = 500 V (Note 1)	> 10 <sup>9</sup>	Ω

1. Safety limit values - maximum values allowed in the event of a failure.

#### ABSOLUTE MAXIMUM RATINGS (Note 2)

Symbol	Parameter	Value	Units
T <sub>STG</sub>	Storage Temperature	-55 to +150	°C
T <sub>OPR</sub>	Operating Temperature	-55 to +110	°C
ТJ	Junction Temperature	-55 to +125	°C
T <sub>SOL</sub>	Lead Solder Temperature (Refer to Reflow Temperature Profile)	260 for 10 sec	°C
Emitter			
I <sub>F(average)</sub>	Continuous Forward Current	50	mA
I <sub>F(peak)</sub>	Peak Forward Current (1 µs pulse, 300 pps)	1	А
V <sub>R</sub>	Reverse Input Voltage	6	V
PD <sub>LED</sub>	Power Dissipation (Note 3)	70	mW
Detector			
I <sub>C(average)</sub>	Continuous Collector Current	50	mA
V <sub>CEO</sub>	Collector-Emitter Voltage	80	V
V <sub>ECO</sub>	Emitter-Collector Voltage	7	V
PDC	Collector Power Dissipation (Note 3)	150	mW

2. Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 3. Functional operation under these conditions is not implied. Permanent damage may occur if the device is subjected to conditions outside

these ratings.

### ELECTRICAL CHARACTERISTICS

 $T_A = 25^{\circ}C$  unless otherwise specified

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
Emitter					•	
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 20 mA		1.2	1.4	V
I <sub>R</sub>	Reverse Current	$V_{R} = 4 V$			10	μA
CT	Terminal Capacitance	V = 0 V, f = 1 kHz		30	250	pF
Detector				·		
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{C} = 0.1 \text{ mA}, I_{F} = 0 \text{ mA}$	80			V
BV <sub>ECO</sub>	Emitter-Collector Breakdown Voltage	$I_{E} = 10 \ \mu A, \ I_{F} = 0 \ m A$	7			V
I <sub>CEO</sub>	Collector Dark Current	$V_{CE} = 50 \text{ V}, \text{ I}_{F} = 0 \text{ mA}$			100	nA

#### TRANSFER CHARACTERISTICS TA=25°C unless otherwise specified

Symbol	Parameter	Device	Conditions	Min.	Тур.	Max.	Units
		FODM217A		80		160	
CTR <sub>CE</sub>	Current Transfer Ratio (collector-emitter)	FODM217B	<sup>I</sup> F = 5 mA, <sup>V</sup> CE = 5 V	130		260	%
- CE		FODM217C		200		400	
		FODM217D		300		600	
Ι <sub>C</sub>	Collector Current	All	I <sub>F</sub> = 5 mA, V <sub>CE</sub> = 5 V	4		30	mA
CTR <sub>(SAT)</sub>	Saturated Current Transfer Ratio	All	<sup>I</sup> F = 8 mA, <sup>V</sup> CE = 0.4 V		60		%
I <sub>C(SAT)</sub>	Collector Current	All	I <sub>F</sub> = 8 mA, V <sub>CE</sub> = 0.4 V		4.8		mA
V <sub>CE(SAT)</sub>	Collector-Emitter Saturation Voltage	All	<sup>I</sup> F = 8 mA, <sup>I</sup> C = 2.4 mA			0.4	V

#### SWITCHING CHARACTERISTICS

T<sub>A</sub>=25°C unless otherwise specified

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
t <sub>ON</sub>	Turn On Time	<sup>I</sup> C = 2 mA, <sup>V</sup> CE = 10 V,		3		μs
ON		R <sub>L</sub> = 100 Ω				P
t <sub>OFF</sub>	Turn Off Time	$^{\rm I}{\rm C}$ = 2 mA, $^{\rm V}{\rm CE}$ = 10 V,		3		μs
011		R <sub>L</sub> = 100 Ω				
<sup>t</sup> R	Output Rise Time (10% -90%)	$I_{C} = 2 \text{ mA}, V_{CE} = 10 \text{ V},$		2		μs
K		R <sub>L</sub> = 100 Ω		2		40
t <sub>F</sub>	Output Fall Time (90% -10%)	$I_{C} = 2 \text{ mA}, V_{CE} = 10 \text{ V},$		3		μs
·		R <sub>L</sub> = 100 Ω				
SOLATIC	ON CHARACTERISTICS	•	•	•	•	•

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V <sub>ISO</sub>	Input-Output Isolation Voltage	Freq = 60 Hz, t = 1.0 min, I <sub>I-O</sub> ≤ 10 µA (Note 4,5)	3,750			VAC <sub>RMS</sub>
R <sub>ISO</sub>	Isolation Resistance	V <sub>I-O</sub> = 500 V (Note 4)	5 x 10 <sup>10</sup>			Ω
C <sub>ISO</sub>	Isolation Capacitance	Frequency = 1 MHz		0.6	1.0	pF

4. Device is considered a two terminal device: Pin 1 and 2 are shorted together and Pins 3 and 4 are shorted together.

5. 3,750 VAC<sub>RMS</sub> for 1 minute duration is equivalent to 4,500 VAC<sub>RMS</sub> for 1 second duration.

#### **TYPICAL CHARACTERISTICS**

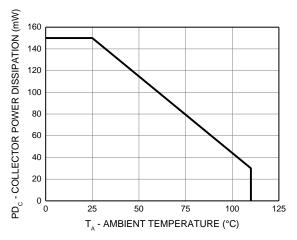


Figure 1. Collector Power Dissipation vs. Ambient Temperature

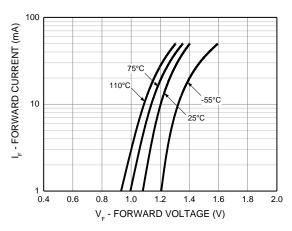


Figure 3. Forward Current vs. Forward Voltage

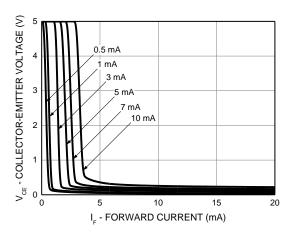


Figure 5. Collector Emitter Voltage vs. Forward Current

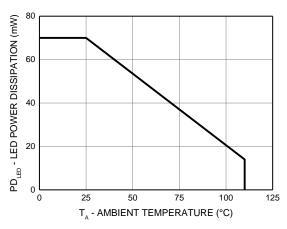


Figure 2. LED Power Dissipation vs. Ambient Temperature

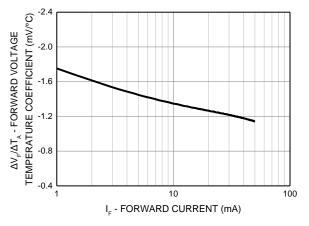
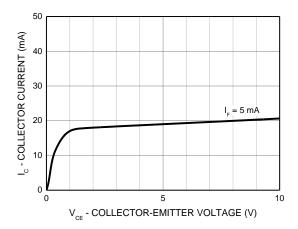
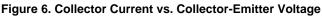


Figure 4. Forward Voltage Temperature Coefficient vs. Forward Current





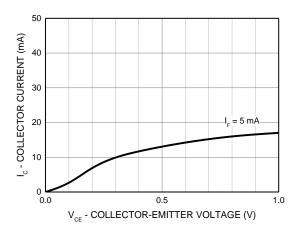


Figure 7. Collector Current vs. Small Collector-Emitter Voltage

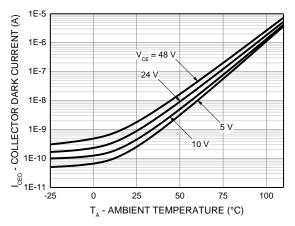


Figure 9. Collector Dark Current vs. Ambient Temperature

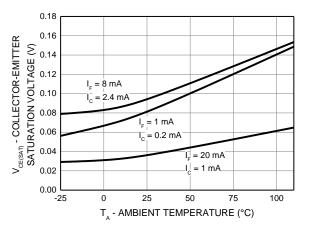


Figure 11. Collector-Emitter Saturation vs. Ambient Temperature

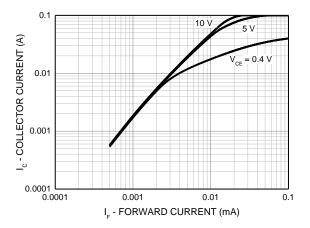


Figure 8. Collector Current vs. Forward Current

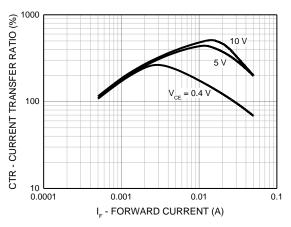


Figure 10. Current Transfer Ratio vs. Forward Current

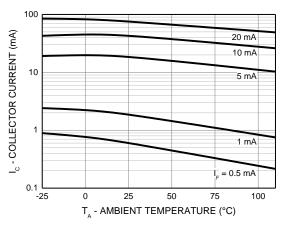


Figure 12. Collector Current vs. Ambient Temperature

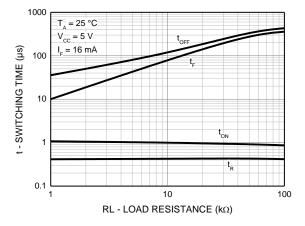


Figure 13. Switching Time vs. Load Resistance

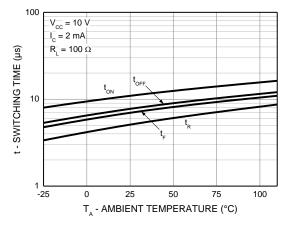


Figure 14. Switching Time vs. Ambient Temperature

**TEST CIRCUIT** 

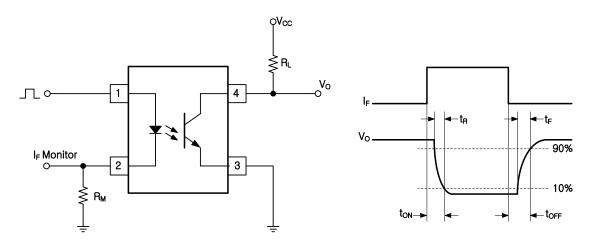
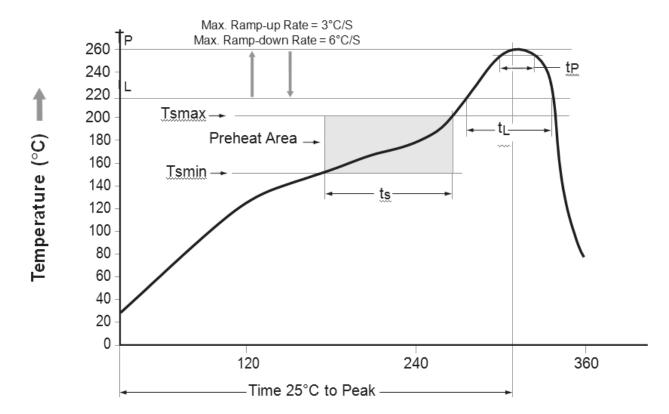


Figure 15. Test Circuit for Switching Time

### **REFLOW PROFILE**



Profile Freature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (t <sub>S</sub> ) from (Tsmin to Tsmax)	60–120 seconds
Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )	3°C/second max.
Liquidous Temperature (T <sub>L</sub> )	217°C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60–150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

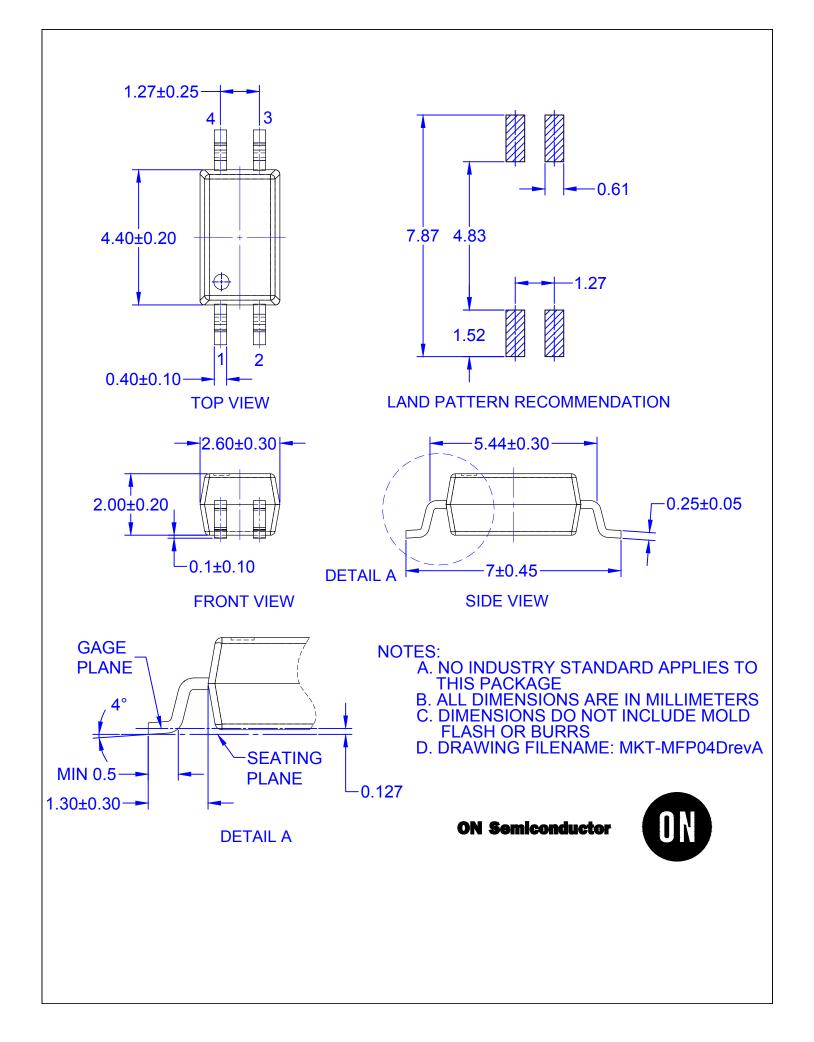
Figure 36. Reflow Profile

## FODM217 Series

#### **ORDERING INFORMATION** (Note 6)

Part Number	Package	Packing Method
FODM217A	SOP 4-Pin	Tube (100 units)
FODM217AR2	SOP 4-Pin	Tape and Reel (3000 units)
FODM217AV	SOP 4-Pin, DIN EN/IEC60747-5-5 Option (pending approval)	Tube (100 units)
FODM217AR2V	SOP 4-Pin, DIN EN/IEC60747-5-5 Option (pending approval)	Tape and Reel (3000 units)

6. The product orderable part number system listed in this table also applies to the FODM217B, FODM217C, and FODM217D products.



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